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**AMENDMENTS TO THE SPECIFICATION**

(1) Please replace the paragraph beginning at page 3, line 26, with the following amended paragraph:

However, it will be recognized that the invention finds utility in association with semiconductor fabrication generally, and that the invention is thus not limited to any particular embodiment or implementation disclosed and described herein.

(2) Please replace the paragraph beginning at page 5, line 4 with the following amended paragraph:

The device model 204 is connected to the overetch ~~system~~ controller 202. The device model 204 is a software based model of the target device 203 and can include all of the information included in optical process correction (OPC) library cells or models. The device model 204 is based on the chip design and layout of the target device 203. It is appreciated that a single chip design can have a number of different layouts. Thus, the device model 204 can have information based on a variety of layouts for a single chip design. However, layouts are constrained by design rules such as, but not limited to, minimum pitch, line width, spacing and the like. These rules are included in the device model 204 in order to ensure that they are not broken by an overetch process. A number of adjustable parameters, such as, percent etchable area and pattern density are also included in the device model 204. The device model 204 is able to characterize, provide or set parameters such as overetch etch rate, critical dimensions (CD), maximum acceptable oxide loss, minimum uniformity and the like. It is appreciated that the information contained in the device model 204 can be modified by the controller 202.